

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.

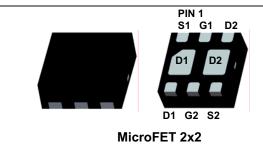


## FDMA1028NZ

### Dual N-Channel PowerTrench<sup>®</sup> MOSFET

### **General Description**

This device is designed specifically as a single package solution for dual switching requirements in cellular handset and other ultra-portable applications. It features two independent N-Channel MOSFETs with low on-state resistance for minimum conduction losses. The MicroFET 2x2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.



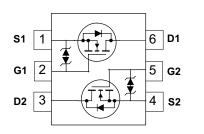
### Features

■ 3.7 A, 20V.  $R_{DS(ON)} = 68 \text{ m}\Omega @ V_{GS} = 4.5V$  $R_{DS(ON)} = 86 \text{ m}\Omega @ V_{GS} = 2.5V$ 

Low profile – 0.8 mm maximum – in the new package MicroFET 2x2 mm

July 2014

- HBM ESD protection level > 2kV (Note 3)
- RoHS Compliant
- Free from halogenated compounds and antimony oxides



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DS</sub>	Drain-Source Voltage		20	V
V <sub>GS</sub>	Gate-Source Voltage		±12	V
I <sub>D</sub>	Drain Current – Continuous	(Note 1a)	3.7	A
	– Pulsed		6	
PD	Power Dissipation for Single Operation	(Note 1a)	1.4	W
		(Note 1b)	0.7	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C
Therma	I Characteristics	·		•
<b>D</b>	Thermal Desistance, Junction to Ambient		96 (Single Operation)	

D Thermal Desistance Junction to Ambient (11, 11) (Single Operation)	
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient(Note 1b)173 (Single Operation)	
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient (Note 1c) 69 (Dual Operation)	
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient (Note 1d) 151 (Dual Operation)	

### Package Marking and Ordering Information

028 FDMA1028NZ 7" 8mm 3000 unit	Device Marking	Device Marking Device Reel Size		Tape width	Quantity	
	028	FDMA1028NZ	7"	8mm	3000 units	

©20F3 Fairchild Semiconductor Corporation

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		•			
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V$ , $I_D = 250 \mu A$	20			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 µA, Referenced to 25°C		15		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 16 V$ , $V_{GS} = 0 V$			1	μA
I <sub>GSS</sub>	Gate–Body Leakage	$V_{GS} = \pm 12 V$ , $V_{DS} = 0 V$			±10	μA
	acteristics (Note 2) Gate Threshold Voltage		0.6	1.0	1.5	V
V <sub>GS(th)</sub>	ů	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	0.6	1.0	1.5	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 µA, Referenced to 25°C		-4		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source	$V_{GS} = 4.5 V$ , $I_D = 3.7 A$		37	68	mΩ
	On–Resistance	$V_{GS} = 2.5 V$ , $I_D = 3.3 A$		50	86	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.7 A, T <sub>J</sub> =125°C		53	90	
<b>g</b> fs	Forward Transconductance	$V_{DS} = 10 V$ , $I_{D} = 3.7 A$		16		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = 10 V$ , $V_{GS} = 0 V$ ,		340		pF
Coss	Output Capacitance	f = 1.0 MHz		80		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1		60		pF
Rg	Gate Resistance				25	Ω

### Switching Characteristics (Note 2)

t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DD</sub> = 10 V,		8	16	ns
t <sub>r</sub>	Turn–On Rise Time	V <sub>GS</sub> = 4.5 V,	$R_{GEN}$ = 6 $\Omega$	8	16	ns
t <sub>d(off)</sub>	Turn–Off Delay Time	-		14	26	ns
t <sub>f</sub>	Turn–Off Fall Time	-		3	6	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 10 V,	I <sub>D</sub> = 3.7 A,	4	6	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		0.7		nC
$Q_{gd}$	Gate-Drain Charge			1.1		nC

FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

FDMA1028NZ Rev B7

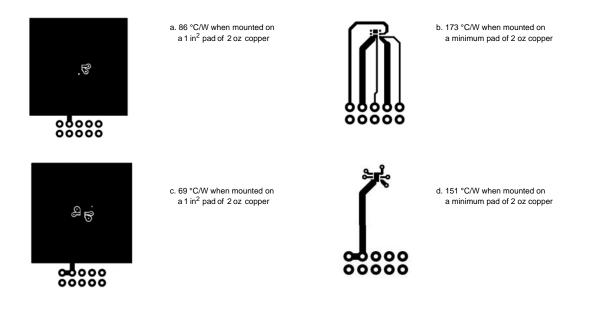
# FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

### **Electrical Characteristics** $T_J = 25 \degree C$ unless otherwise noted

### Notes:

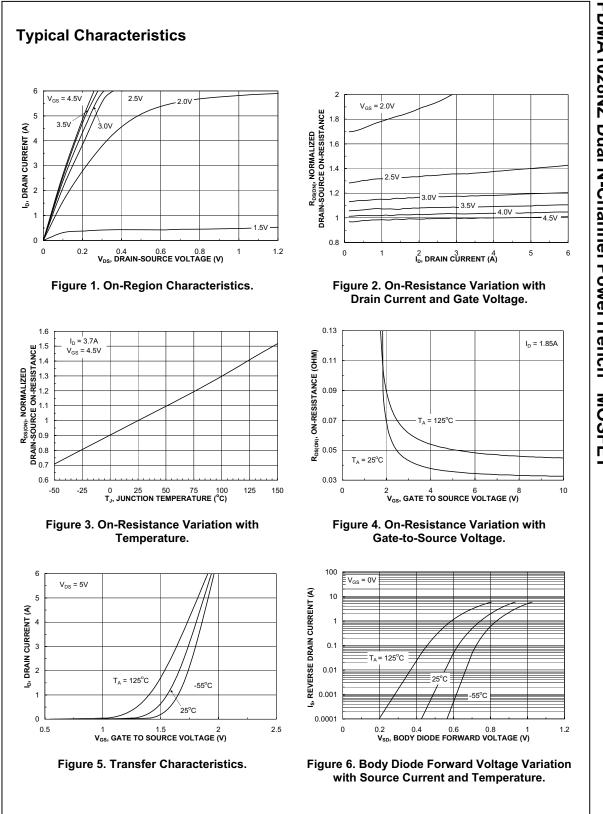
1. R<sub>8JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>8JA</sub> is guaranteed by design while R<sub>8JA</sub> is determined by the user's board design. (a)  $R_{0JA} = 86 \text{ °C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For single operation.

- (b) R<sub>BJA</sub> = 173 °C/W when mounted on a minimum pad of 2 oz copper. For single operation.
- (c)  $R_{0JA} = 69 \text{ °C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For dual operation.
- (d)  $R_{\theta JA}$  = 151  $^{o}\text{C/W}$  when mounted on a minimum pad of 2 oz copper. For dual operation.



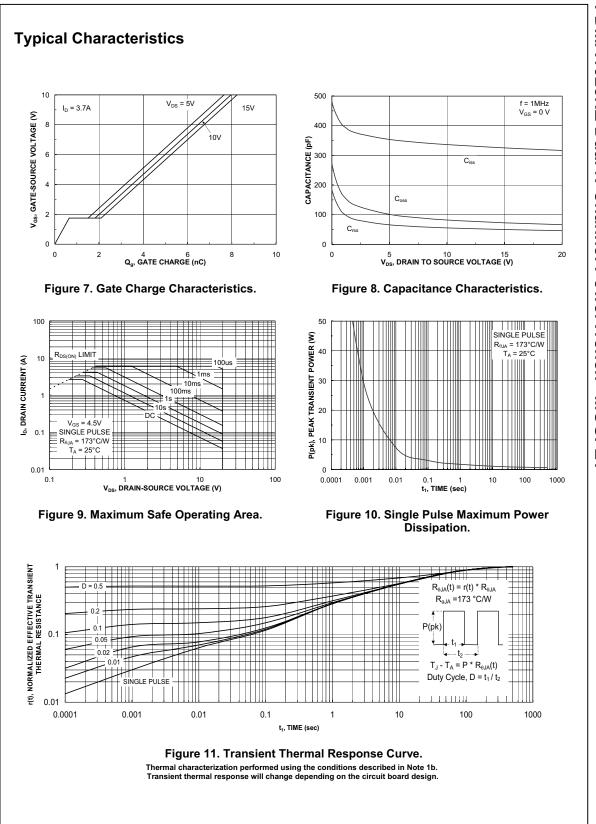
2. Pulse Test : Pulse Width < 300 us, Duty Cycle < 2.0%

3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.



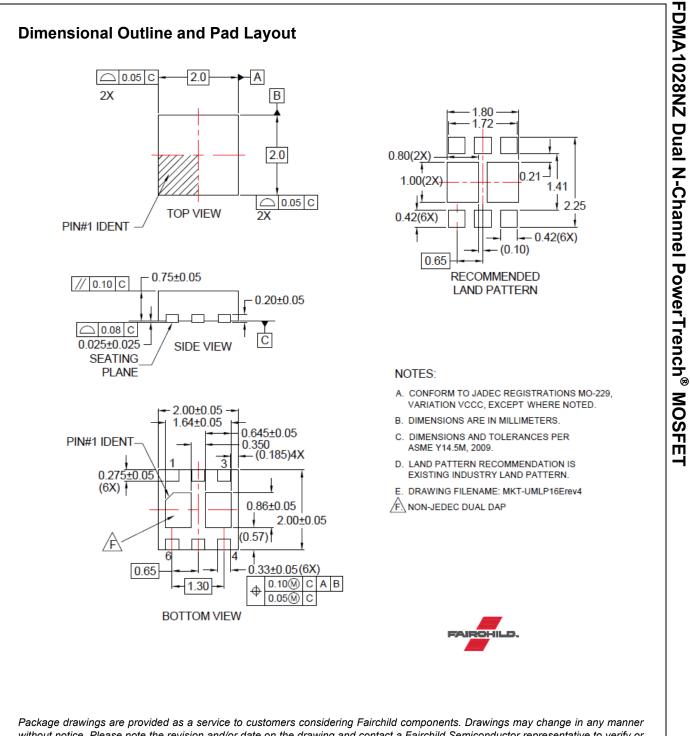
FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

FDMA1028NZ Rev B7



FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

FDMA1028NZ Rev B7



Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_MLDEB-X06



Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

### PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: <u>FDMA1028NZ</u>